

L9	26	7 and spaced adj location	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/21 17:29
L10	0	9 and pond adj pad	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/21 17:29
L11	1333	365/158.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/21 17:29
L12	1	11 and dielectric adj encapsulant	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/21 17:30
L13	1	recess with dielectric adj encapsulant with conductive adj element with adjacent adj conductive adj element.clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/21 17:32
L14	0	severance adj region with conductive adj lead with mutually adj electrically adj isolated.clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/21 17:33

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	128587	semiconductor and package	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/21 17:16
L2	114	1 and array and electrically and isolated adj conductive and adjacent and outer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/21 17:21
L3	4	2 and dielectric adj encapsulant	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/21 17:30
L4	4	3 and recess	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/21 17:23
L5	2502640	1 and laed afj frame	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/21 17:23
L6	2536702	1 and lead afj frame	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/21 17:25
L7	17531	1 and lead adj frame	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/21 17:27
L8	4	7 and severance adj region	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/21 17:28